

## Product Overview

### MC14012B: Dual 4-Input NAND Gates

For complete documentation, see the data sheet.

These Dual 4 Input NAND Gates are constructed with P and N channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

### Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range.
- Double Diode Protection on All Inputs
- Pin-for-Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- Pb-Free Packages are Available\*

### Part Electrical Specifications

Product	Compliance	Status	Type	Channels	V <sub>CC</sub> Min (V)	V <sub>CC</sub> Max (V)	t <sub>pd</sub> Max (ns)	I <sub>O</sub> Max (mA)	Package Type
MC14012BDG	Pb-free	Active	NAND	2	3	18	130	null	SOIC-14
	Halide free								
MC14012BDR2G	Pb-free	Active	NAND	2	3	18	130	null	SOIC-14
	Halide free								
NLV14012BDG	AEC Qualified	Active	NAND	2	3	18	null	null	SOIC-14
	PPAP Capable								
	Pb-free								
	Halide free								
NLV14012BDR2G	AEC Qualified	Active	NAND	2	3	18	null	null	SOIC-14
	PPAP Capable								
	Pb-free								
	Halide free								

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Created on: 6/18/2019